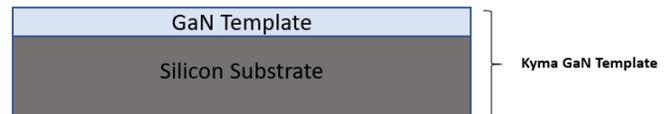




GaN Templates on Silicon

Kyma's Gallium Nitride (GaN) templates are grown by HVPE and provide a high purity (carbon-free) GaN buffer for subsequent device epitaxy. GaN templates are used for:

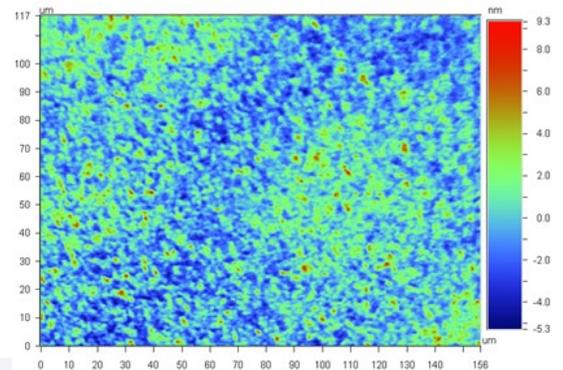
- Subsequent epitaxial growth studies or device efforts
- GaN fabrication process development activities
- Basic research of GaN



Template Detail:

Dopant	Unintentionally Doped (UID)
Resistivity	<5 Ohm-cm
Orientation	c-axis (00.1) ± 1.0°
Available Sizes	2"-200mm
Available Thicknesses	Up to 500nm

GaN Template Specifications:	Production	Rider**
Thickness Uniformity:	<10%	n/a
Edge Cracking:	none	n/a
Surface Finish:	As grown	As grown



500nm GaN on Si as-grown surface measured by Wyko (117x156 microns)

***Rider grade templates are GaN templates which have missed one or more of Kyma's specifications and are sold from existing stock and may have limited availability—inquire for details on current availability*